

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-18. (Canceled)

19. (Currently Amended) A method of producing laterally integrated semiconductor components, comprising the steps of:

applying at least one first semiconductor component on an epitaxial substrate;

layering a ~~hydrogen fluoride soluble~~ mask over said at least one first semiconductor component and said substrate, said mask defining one or more windows to said substrate; and

applying at least one other semiconductor component in at least one of said one or more windows; and

removing said mask layer by introduction of at least one fluoride based compound into an epitaxy reactor.

20. (Previously Presented) The method according to claim 19, wherein said mask includes at least one thinner mask portion where said one or more windows are to be defined and at least one thicker mask portion covering said at least one first semiconductor component, and wherein said step of layering comprises removing at least said at least one thinner mask portion so as to expose said one or more windows.

21. (Currently Amended) The method according to claim 19, wherein each of said steps is performed within ~~an~~ the epitaxy reactor.

22. (Previously Presented) The method according to claim 21, further comprising initially cleaning said substrate within said epitaxy reactor by corrosion of any hydrogen fluoride

soluble layers through introduction of at least one fluoride based compound.

23. (Previously Presented) The method according to claim 19, wherein said step of layering comprises layering N mask layers over said first semiconductor component and said substrate, wherein each of said N mask layers defines at least one window to one or more from a group consisting of an underlying mask layer and said substrate, wherein said mask defines at least one first window to said substrate, wherein N is a natural number, and wherein said step of applying at least one other semiconductor component comprises applying at least one second semiconductor component in said at least one first window.

24. (Previously Presented) The method according to claim 23, said method further comprising:

etching at least one of said N mask layers by use of an etchant, such that at least one second window to said substrate is defined; and

repeating said step of applying at least one other semiconductor component to apply at least one third semiconductor component in said at least one second window.

25. (Previously Presented) The method of according to claim 24, further comprising: repeating said etching step and said step of applying at least one other semiconductor component alternately until at least one Nth window to said substrate is defined and at least one (N+1)th semiconductor component is applied in said at least one Nth window.

26. (Previously Presented) The method according to claim 25, wherein after said at least one (N+1)th semiconductor component is applied in said at least one Nth window, any remaining mask layers are removed by etching.

27. (Currently Amended) The method according to claim 25, wherein at least said etching step is performed within an the epitaxy reactor.

28. (Cancelled)

29. (Currently Amended) The method according to claim ~~28~~27, wherein said etchant comprises an unstable fluoride combination which disintegrates into hydrogen fluoride within said epitaxy reactor.

30. (Previously Presented) The method according to claim 19, wherein said first semiconductor component is an electrical component and said other semiconductor component is an optoelectrical component.

31. (Previously Presented) A method for producing laterally integrated semiconductor components comprising the steps of:

applying a mask comprising N masking layers on an epitaxial substrate, wherein each of said N masking layers defines one or more windows for later application of at least one other semiconductor component, wherein said mask defines at least one first window to said substrate, and wherein N is a natural number;

applying at least one first semiconductor component on said substrate in said at least one first window; and

etching by use of an etchant at least one of said N masking layers to expose at least one other window to said substrate;

applying at least one other semiconductor component in said at least one other window; and

if necessary, repeating said steps of etching at least one of said N masking layers and applying at least one other semiconductor component until at least one Nth semiconductor component is applied in at least one Nth window.

32. (Previously Presented) The method according to claim 31, wherein after said at least one Nth semiconductor component has been applied, any remaining mask is removed by etching.

33. (Previously Presented) The method according to claim 31, wherein each of said steps is performed within an epitaxy reactor.

34. (Previously Presented) The method according to claim 33, wherein said step of etching includes introduction of said etchant into said epitaxy reactor.

35. (Previously Presented) The method according to claim 34, wherein said N masking layers are hydrogen fluoride soluble masking layers, and wherein said etchant contains fluoride.

36. (Previously Presented) The method according to claim 35, wherein said etchant comprises an unstable fluoride combination which disintegrates into hydrogen fluoride within said epitaxy reactor.

37. (Previously Presented) The method according to claim 33, further comprising a step of initially cleaning said substrate within said epitaxy reactor by corrosion of any hydrogen fluoride soluble layers through introduction of at least one fluoride based compound.

38. (Previously Presented) The method according to claim 31, wherein said at least one first semiconductor component is different from said at least one other semiconductor component.

39. (Previously Presented) The method according to claim 38, wherein said at least one first semiconductor component is an electrical component and said at least one other semiconductor component is an optoelectronic component.

40. (Previously Presented) The method according to claim 31, wherein said etchant comprises hydrogen fluoride.

41. (Previously Presented) The method according to claim 31, wherein said N masking layers comprises masking layers having different thicknesses.

42. (Previously Presented) The method according to claim 31, wherein said N masking layers comprises masking layers having different compositions.

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43. (New) The method of claim 19, further comprising:  
cooling walls of the epitaxy reactor prior to removing said mask layer.

Amendments to the Drawings:

The attached replacement sheets of drawings includes changes to Figs. 1a. 2c. 3a-3c and 4a-4c.

In Fig. 1a, layer 3 has been corrected to represent a layer.

In Fig. 2c, the German phrase  $\text{NF}_3$ -Ätzgas has been translated to English. The  $\text{NF}_3$  portion of has been deleted.

In. Figs. 3a-3c and 4a-4c, shading has been applied to various items.

All of the drawings have been made formal.